

Title (en)

PERFORATED SILICON MEMBRANE PROVIDED BY AN ELECTROCHEMICAL ETCHING METHOD

Title (de)

PERFORIERTE SILIZIUM-MEMBRAN, HERGESTELLT MITTELS EINES ELEKTROCHEMISCHEN ÄTZVERFAHRENS

Title (fr)

MEMBRANE EN SILICIUM PERFOREE PRODUITE SELON UN PROCEDE D'ATTAQUE ELECTROCHIMIQUE

Publication

EP 1084285 A1 20010321 (DE)

Application

EP 99929077 A 19990503

Priority

- DE 9901292 W 19990503
- DE 19820756 A 19980508

Abstract (en)

[origin: DE19820756C1] A perforated workpiece, comprising a silicon substrate (1) having a first region (6) with through-pores (4) and a second region (7) with blind pores, is new. An Independent claim is also included for producing a perforated workpiece by electrochemically etching one face (2) of a silicon substrate (1) to form pores (4) of depth less than the substrate thickness, providing the opposite substrate face (3) with a mask layer which exposes first regions (6) of this opposite substrate face, etching the exposed face regions (6) to the bottoms of the pores (4) and then removing the mask layer.

IPC 1-7

C25F 3/12

IPC 8 full level

C25F 3/12 (2006.01); **C25F 3/02** (2006.01); **H01P 1/20** (2006.01)

CPC (source: EP KR US)

C25F 3/02 (2013.01 - EP US); **C25F 3/12** (2013.01 - KR); **H01P 1/20** (2013.01 - EP US); **Y10T 428/24273** (2015.01 - EP US); **Y10T 428/24331** (2015.01 - EP US)

Citation (search report)

See references of WO 9958746A1

Cited by

MD2449G2

Designated contracting state (EPC)

DE FR GB IT NL

DOCDB simple family (publication)

DE 19820756 C1 19991111; DE 59906526 D1 20030911; EP 1084285 A1 20010321; EP 1084285 B1 20030806; JP 2002514689 A 20020521; KR 20010052320 A 20010625; TW 552322 B 20030911; US 6558770 B1 20030506; WO 9958746 A1 19991118

DOCDB simple family (application)

DE 19820756 A 19980508; DE 59906526 T 19990503; DE 9901292 W 19990503; EP 99929077 A 19990503; JP 2000548533 A 19990503; KR 20007012422 A 20001107; TW 88106375 A 19990421; US 70827700 A 20001108